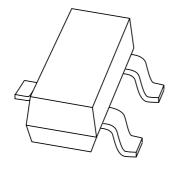
### DISCRETE SEMICONDUCTORS

# DATA SHEET



# PMBD6050 High-speed diode

Product data sheet Supersedes data of 1999 May 11 2004 Jan 14



### **High-speed diode**

### **PMBD6050**

#### **FEATURES**

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

### **APPLICATIONS**

• High-speed switching in thick and thin-film circuits.

### **DESCRIPTION**

The PMBD6050 is a high-speed switching diode fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

#### **MARKING**

TYPE NUMBER	MARKING CODE(1)
PMBD6050	*5A

#### Note

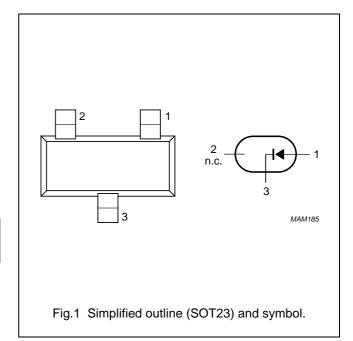
1. \* = p : Made in Hong Kong.

\* = t : Made in Malaysia.

\* = W : Made in China.

#### **PINNING**

PIN	DESCRIPTION		
1	anode		
2	not connected		
3	cathode		



### **ORDERING INFORMATION**

TYPE		PACKAGE					
NUMBER	NAME	DESCRIPTION	VERSION				
PMBD6050	_	plastic surface mounted package; 3 leads	SOT23				

# High-speed diode

PMBD6050

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>RRM</sub>	repetitive peak reverse voltage		_	85	V
$V_R$	continuous reverse voltage		-	70	V
I <sub>F</sub>	continuous forward current	note 1; see Fig.2	_	215	mA
I <sub>FRM</sub>	repetitive peak forward current		-	500	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

### Note

1. Device mounted on an FR4 printed-circuit board.

# High-speed diode

PMBD6050

### **ELECTRICAL CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>F</sub>	forward voltage	see Fig.3		
		I <sub>F</sub> = 1 mA	715	mV
		I <sub>F</sub> = 10 mA	855	mV
		I <sub>F</sub> = 50 mA	1	V
		I <sub>F</sub> = 150 mA	1.25	V
$I_R$	reverse current	see Fig.5		
		V <sub>R</sub> = 50 V	100	nA
		V <sub>R</sub> = 50 V; T <sub>j</sub> = 150 °C	50	μΑ
C <sub>d</sub>	diode capacitance	$f = 1 \text{ MHz}$ ; $V_R = 0$ ; see Fig.6	1.5	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F$ = 10 mA to $I_R$ = 10 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.7	4	ns
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	1.75	V

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-tp)</sub>	thermal resistance from junction to tie-point		330	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

### Note

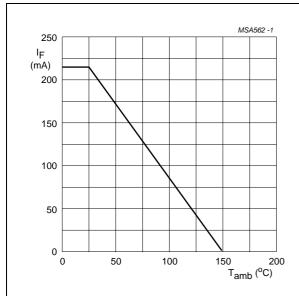
1. Device mounted on an FR4 printed-circuit board.

2004 Jan 14

### High-speed diode

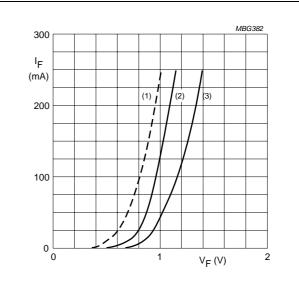
### **PMBD6050**

#### **GRAPHICAL DATA**



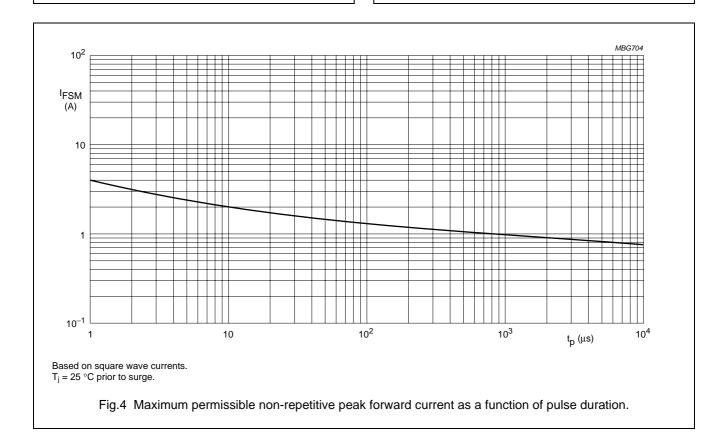
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



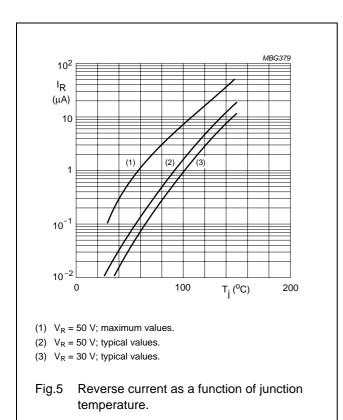
- (1)  $T_i = 150 \,^{\circ}\text{C}$ ; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



## High-speed diode

### **PMBD6050**



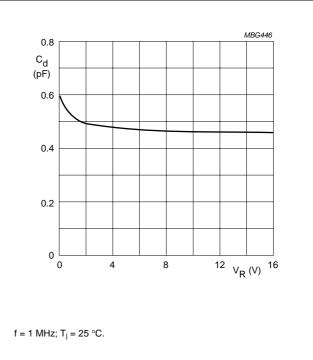
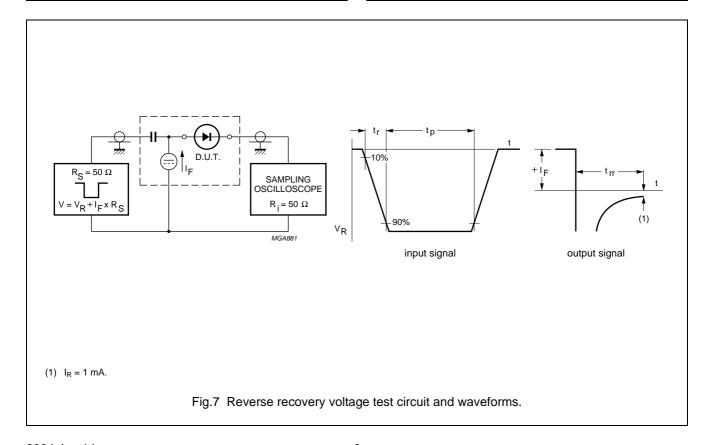
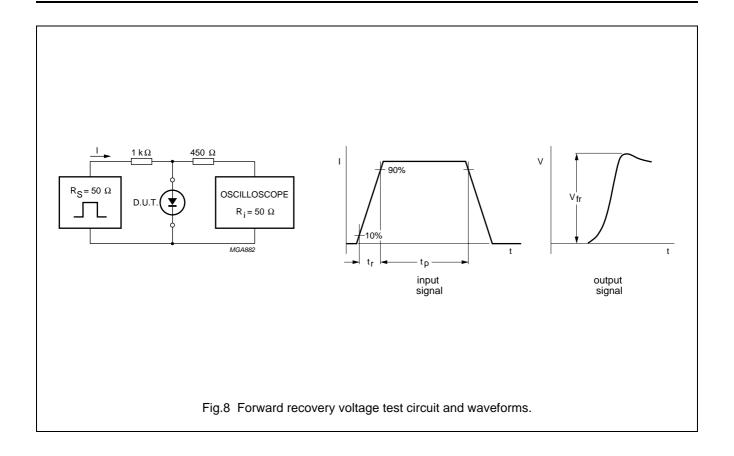


Fig.6 Diode capacitance as a function of reverse voltage; typical values.



# High-speed diode

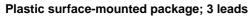
### PMBD6050



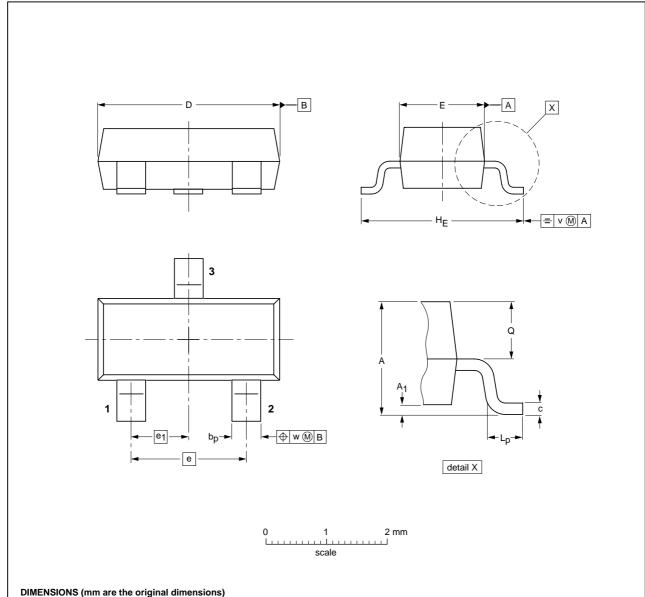
# High-speed diode

PMBD6050

### **PACKAGE OUTLINE**



SOT23



DIMENS	ЮИЗ (П	ım are tı	ne origir	iai dime	ensions)	
						=

UNIT	Α	A <sub>1</sub> max.	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				<del>-04-11-04</del> 06-03-16

### High-speed diode

PMBD6050

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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#### **Contact information**

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